

Designer's Data Sheet

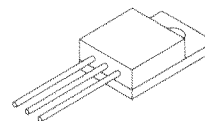
FEATURES:

- Hyper Fast Recovery: 40 nsec Maximum
- PIV to 600 Volts
- Isolated Low Profile Package
- Hermetically Sealed SPD506 Discretes
- Void Free Construction
- For High Efficiency Applications
- For Common Anode Configuration:
SFA40NME-SFA60NME
- For Doubler Configuration:
SFA40DME-SFA60DME
- TX and TXV Level Screening available

**SFA40PME
thru
SFA60PME**

**6 AMP
400-600 VOLTS
40 nsec
HYPER FAST
POSITIVE CENTERTAP
RECTIFIER**

TO-254 (ME)



MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Peak Repetitive Reverse and DC Blocking Voltage SFA40PME SFA50PME SFA60PME	VRRM VRWM VR	400 200 600	Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, TA=25°C)	IO	6	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on IO, allow junction to reach equilibrium between pulses, TA=25°C)	IFSM	150	Amps
Operating and storage temperature	Top & Tstg	-65 to +150	°C
Maximum Thermal Resistance Junction to Case	RθJC	2.5	°C/W

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET#: RH0109 A

RMD

SFA40PME thru SFA60PME

PRELIMINARY



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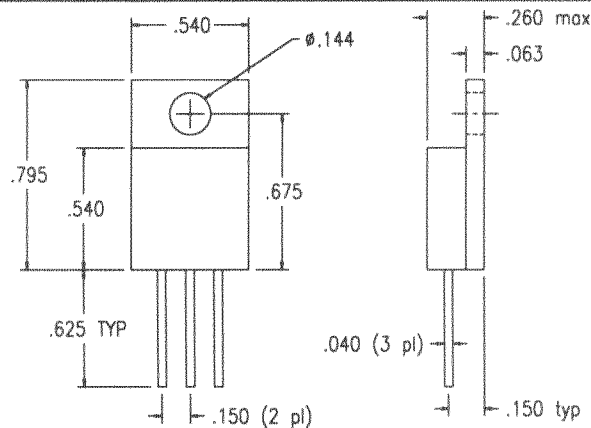
ELECTRICAL CHARACTERISTICS (Per Leg)

CHARACTERISTICS	SYMBOL	MAXIMUM	UNIT
Instantaneous Forward Voltage Drop (IF = 6 Adc, TA=25°C, 300μs Pulse)	VF	1.35	Vdc
Instantaneous Forward Voltage Drop (IF = 6 Adc, TA= - 55°C, 300μs Pulse)	VF	1.5	Vdc
Reverse Leakage Current (Rated VR, TA=25°C, 300μs pulse minimum)	IR	20	μA
Reverse Leakage Current (Rated VR, TA=100°C, 300μs pulse minimum)	IR	5	mA
Junction Capacitance (VR = 10 Vdc, TA=25°C, f= 1 MHz)	CJ	100	pf
Reverse Recovery Time (IF=500mA, IR=1 A, IRR=250mA, TA=25°C)	trr	40	nsec

CASE OUTLINE: EPOXY TO-254

PIN OUT:

PIN 1: Anode 1
PIN 2: Cathode
PIN 3: Anode 2



TYPICAL OPERATING CURVES

TA=25°C Unless otherwise specified

